TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT Docket No.			
(Under 37 CFR 1.97(b) or 1.97(c)) PECE/L/SEC.875		CUE/LISEC.875	
In Re Application Of: Young Goo LEE et al.	ñ/	in .	
In Re Application Of: Young Goo LEE et al. JUL 3 0 2003 Filing Date Examiner From Art Unit			
Serial No. Filling Date	Evenine	CEHIER SOUD	
Serial No. 78ADEMAN December 28, 2001		Group / tit Gritt	
	TBA	2812	
Title: METHOD OF FABRICATING SEMICONDUCTOR DEVICE FOR PREVENTING CONTAMINATING			
PARTICLE GENERATION			
Address			
Address to: Assistant Commissioner for Patents			
Washing	gton, D.C. 20231	001-	
Washington, D.C. 20231 COPY			
1. The Information Disclosure Statement submitted herewith is being filed within three months of the filing			
of a national application other than a continued	prosecution application under :	37 CFR 1.53(d); within	
three months of the date of entry of the nationa application; before the mailing of a first Office Ad	I stage as set forth in 37 CFR 1 ction on the merits, or hefore the	.491 in an international	
Action after the filing of a request for continued e	examination under 37 CFR 1.114		
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37 CFR 1.97(c)			
CFR 1.97(b), provided that the Information Disclosure Statement is filed before the mailing date of a			
Final Action under 37 CFR 1.113, a Notice of Allowance under 37 CFR 1.311, or an Action that			
otherwise closes prosecution in the application, and is accompanied by one of:			
☐ the statement specified in 37 CFR 1.97(e);			
OR			
the fee set forth in 37 CFR 1.17(p).			
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TRANSMITTAL OF INFORMATION DISCLO	7(0)	Docket No.		
(Under 37 CFR 1.97(b) or 1.97(c)) RF(F) SEC.875				
In Re Application: Young-Goo LEE et al.	AUG - 1 21	 003		
Serial No. Filling Date	TECHNOLOGY CERT Examiner	ER 2300 Group Art Unit		
10/029,147 TRADEMAN December 28, 2001	ТВА	2812		
METHOD OF FABRICATING SEMICONDUCTO	OR DEVICE FOR PREVENTIN	IG		
PARTICLE GENERATION	_			
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Payment of Fee				
(Only complete if Applicant e	lects to pay the fee set forth in 37 C	FR 1.17(p))		
☐ A check in the amount of is attached.				
☐ The Assistant Commissioner is hereby authorized to charge and credit Deposit Account No. as described below. A duplicate copy of this sheet is enclosed.				
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I certify that this document and authorization to charge deposition account is being facsimile transmitted to the United State Patent and Trademark Office (F	as first class mail und	I certify that this document and fee is being deposited with the U.S. Postal Service as first class mail under 37 C.F.R. 1.8 and is addressed to the Assistant Commissioner for Patents, Washington, D.C. 20231.		
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Typed or Printed Name of Person Signing Certificate	Typed or Printed Name of	of Person Mailing Certificate		
*This certificate may only be used if paying by deposit account Signature ADAM C. VOLENTINE REG. NO. 33,289	Dated: MARCH 31, 200	3		
VOLENTINE FRANCOS, P.L.L.C.				
12200 SUNRISE VALLEY DRIVE, SUITE 150				
RESTON, VA 20191				
TEL. NO.: (703) 715-0870				
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ATTY DOCKET #: SEC.875

DUE DATE:

APPLICANT: Young-Goo Lee et al.

SERIAL NO.: 10/029,147

FILING DATE: December 28, 2001

TITLE:

METHOD OF FABRICATING SEMICONDUCTOR DEVICE FOR

PREVENTING CONTAMINATING PARTICLE GENERATION

RECEIPT OF THE FOLLOWING PAPERS IS ACKNOWLEDGED:

Transmittal of Information Disclosure Statement, PTO-1449 Form,

1 reference.

DATE: March 31, 2003

Check No. N/A]